Experimental and Theoretical Study of PXRC (Parametric X-Radiation at Channeling) from 255 MeV Electrons in Si

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## **Radiation types from channeled particle in a crystal**

#### **Terminology (definitions):**

**PXR** = Parametric X-Radiation = diffraction of relativistic electron electromagnetic field (virtual photons) on the crystal = system of crystallographic planes = well known since first experimental observation (1985, Tomsk, electron synchrotron "Sirius")

**DCR** = Diffracted Channeling Radiation (Nitta et al, 2002-2008; Bogdanov-Korotchenko-Pivovarov et al, JETP Letters, 2007) ... . Diffraction of (virtual) channeling radiation.

**PXRC** = Parametric X-Radiation from channeled electrons (H.Nitta et al , 1996) limiting case of DCR. Diffraction of channeled relativistic electron electromagnetic field (virtual photons) on the crystal. Electron is bound with channeling plane.

**PXR vs PXRC**: plane waves vs "squeezed states" (quantum states) bound to channeling planes  $\rightarrow$  **quantum** difference ?

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#### **Radiation types from channeled particle in a crystal**

#### H.Nitta: Channeling 2008 → CLASSIFICATION

**Diffracted Channeling Radiation (DCR)** Radiation process and matrix elements Fermi's golden rule:  $w_{IF} = \frac{2\pi}{\hbar} |\langle F | H_{int} | I \rangle|^2 \rho_F$ The interaction Hamiltonian:  $H_{int} = -\frac{e}{\gamma mc} \mathbf{A} \cdot \hat{\mathbf{p}}$ Bloch wave "photon":  $\mathbf{A}(\mathbf{r}) = \sum \sum \mathbf{A}_{\mathbf{g}} \exp[i(\mathbf{k} + \mathbf{g}) \cdot \mathbf{r}] + c.c..$ quantum states of channeled electron:  $\psi^{(s)}(\mathbf{r}) = \frac{1}{\sqrt{L_{x}L_{z}}} \varphi_{n}(y) e^{i\mathbf{p}_{\parallel} \cdot \mathbf{r}_{\parallel}/\hbar} \qquad \varphi_{n}(y) = \frac{1}{\sqrt{L_{y}}} \sum_{G} C_{G}^{(n)}(p_{y}) \exp[i(p_{y}/\hbar + G)]$  $\frac{\mathbf{p}_{\perp}}{2\pi m} + V(y) \quad \varphi_n(y) = E_{\perp,n} \varphi_n(y)$ 

#### **Radiation types from channeled particle in a crystal**

#### H.Nitta: Channeling 2008 → CLASSIFICATION



#### **Radiation types from channeled particle in a crystal**

#### H.Nitta: Channeling 2008 → CLASSIFICATION



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#### **Radiation types from channeled particle in a crystal**

#### H.Nitta: Channeling 2008 → CLASSIFICATION

Diffracted Channeling Radiation (DCR) intraband transition: i=f  $M_{-\mathbf{g}}^{(ii)} = -\left(\frac{e}{c}\right) (\mathbf{A}_{-\mathbf{g}}^* \cdot \mathbf{v}_{\parallel}) F_{ii}((\mathbf{k} - \mathbf{g})_y) \delta(\mathbf{p}_{\parallel} - \mathbf{p}_{\parallel} | \hbar \mathbf{k}_{-\mathbf{g}\parallel})$  $F_{ii}(q) = \langle \varphi_i | e^{-iqy} | \varphi_i \rangle$  form facto  $\left(\frac{dN}{d\theta \, d\theta \, dz}\right) = \frac{\alpha \omega_{\rm B}}{4\pi c \sin^2 \theta_{\rm p}} \left(\frac{\theta_{\rm x}^2}{4(1+W_{\rm s}^2)} + \frac{\theta_{\rm y}^2}{4(1+W_{\rm s}^2)}\right)$  $W_{v\sigma} \equiv \frac{1}{2 |\chi_{\sigma}| P_{\sigma}} \left[ \theta_x^2 + \theta_y^2 + \theta_{kin}^2 - \frac{|\chi_g|^2 P_{\sigma}^2}{\theta_x^2 + \theta_y^2 + \theta_{kin}^2} \right], (\sigma = \parallel, \perp)$  $\theta_{kin}^2 = \gamma^{-2} + |\chi_0|$ 

## **Radiation types from channeled particle in a crystal**

- Interband transitions (i=f) correspond to "DCR" = Diffracted Channeling Radiation
- Intraband transitions (i = f) correspond to "PXRC" = Parametric Xradiation at channeling
- Nitta suggested the form factors of channeled states to be equal approximately to 1
- In this case, angular distribution of PXRC does not differ from that of PXR
- Experiment: SAGA-LS (JETP Letters, 2012)  $\rightarrow$  a difference exists !
- Motivation to re-calculate PXRC angular distribution → a subject of theoretical part of this presentation



## **PXRC at planar channeling**

The PXRC appears when an electron passes through a crystal in the channeling regime. The channeling means that the electron is in a bound state with the crystal plane (axis)





## **PXRC: first experiment**

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#### Quantum Effects for Parametric X-ray Radiation during Channeling: Theory and First Experimental Observation<sup>¶</sup>

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The theory of X-ray radiation from relativistic channeled electrons at the Bragg angles—parametric X-ray radiation (PXR) during channeling (PXRC)—is developed while accounting for two quantum effects: the initial population of bound states of transverse motion and the transverse "form-factor" of channeled electrons. An experiment was conducted using a 255 MeV electron beam from a linac at the SAGA Light Source. We have identified a difference in the angular distributions of PXR and PXRC and obtained a fairly good agreement between the theoretical and experimental results.

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#### **PXRC: first experiment**



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![](_page_10_Picture_0.jpeg)

#### **PXRC: experimental details**

JETP Letters 2012

- Dechanneling in a 20 micrometers Si: H.Backe (Channeling 2010) – negligible ?
- Initial angular spread of 255 electron beam at SAGA-LS:  $\theta_{o} = \theta_{L}/3 \rightarrow \text{could be better}$
- Imaging plate: all reflection orders are detected ? Improvements ?
- Bragg direction: could be even better ?
- Axial channeling ?
- Another crystal (e.g. diamond) ?

![](_page_11_Picture_0.jpeg)

#### **PXRC: experimental results**

Angular distribution of the PXRC and PXR from electron beam with energy 255 MeV at (220) Si channeling (section along  $\theta_x = 0$  and  $\theta_y = 0$ )

![](_page_11_Figure_3.jpeg)

#### **PXRC** from planar channeled electrons (theory)

Angular distribution of PXRC from channeled electron being in a quantum state "n" of transverse motion

$$dN_{\text{PXRC}}^{n} = \frac{d^{3}N_{nn}}{d\theta_{x}d\theta_{y}dz} = dN_{\text{PXR}} |F_{nn}|^{2}$$
$$dN_{\text{PXR}} = \frac{\alpha\omega_{B}}{16\pi c \sin^{2}\theta_{B}} \left[ \frac{\theta_{x}^{2}}{1+W_{\pi}^{2}} + \frac{\theta_{y}^{2}}{1+W_{\sigma}^{2}} \right] \left[ |F_{nn}|^{2} = |\int_{-d/2}^{d/2} \phi_{n}^{*}(y) \exp(-i\omega_{B}\theta_{y}y/c)\phi_{n}(y)dy|^{2} \right]$$

$$W_{\tau} = \frac{1}{2 |\chi_g| P_{\tau}} (R - \frac{|\chi_g|^2 P_{\tau}^2}{R}), \ \tau = (\pi, \sigma),$$

$$R = \left[\theta_x - \frac{\Omega_{if}}{\omega_B} \cos \theta_B\right]^2 + \theta_y^2 + R_o,$$

$$R_{\circ} = \theta_{kin}^2 - 2 \frac{\Omega_{if}}{\omega_B}, \quad \theta_{kin}^2 = \gamma^{-2} + |\chi_0|,$$

 $\phi_n(y)$  is the wave function for planar channeled electrons and *d* is the distance between the channeling planes,  $\alpha = e^2/c\hbar$ 

Key question: what we are looking for comparing PXR and PXRC ? Answer: recent experiment at SAGA-LS

#### **Calculated angular distributions of PXRC and PXR**

(sections along  $\theta_x = 0$ )

![](_page_13_Figure_3.jpeg)

#### **Theory: relative difference of PXR and PXRC**

The PXRC angular distribution = sum over populated quantum states

$$\frac{d^3 N_{\text{PXRC}}}{d\theta_x d\theta_y dz} = dN_{\text{PXR}} \sum_n P_n(\theta_\circ) |F_{nn}|^2$$

Initial population of the n-th energy level

$$P_n(\theta_\circ) = \frac{1}{d} \left| \int_{-d/2}^{d/2} \exp(ik_y \theta_\circ y) \phi_n(y) dy \right|^2$$

Relative difference in PXR and PXRC

$$\delta = \frac{dN_{\text{PXR}} - \sum_{n} dN_{\text{PXRC}}^{n}}{dN_{\text{PXR}}} = 1 - \sum_{n} P_{n}(\theta_{\circ}) |F_{nn}|^{2}$$

#### **Calculation of wave functions, populations & form-factors**

- Single potential well: Poeschl-Teller  $U(y) = -U_{\circ} \cosh^{-2} \lambda y.$
- Levels number  $E_{n\perp} = -U_{\circ}(1+n-s)^2/s(s-1), n < s-1$
- Levels parity
- Levels population

$$\phi_{e}(y) = \cosh^{s} \lambda y_{2} F_{1}(\frac{1}{2} + n, -\frac{1}{2} - n + s; \frac{1}{2}; -\sinh^{2} \lambda y),$$
  
$$\phi_{o}(y) = \cosh^{s} \lambda y \sinh \lambda y_{2} F_{1}(-\frac{1}{2} - n + s, \frac{3}{2} + n; \frac{3}{2}; -\sinh^{2} \lambda y).$$

$$U_{\circ} = \frac{\lambda^{2}\hbar^{2}}{2\gamma m}s(s-1), \quad E_{n\perp} = -\frac{\lambda^{2}\hbar^{2}}{2\gamma m}\kappa^{2}, \quad s = (1+\sqrt{8\gamma m U_{\circ}/\hbar^{2}\lambda^{2}})/2,$$

## **Calculation of wave functions, populations & form-factors**

- Single potential well: Poeschl-Teller
- Level number n=1 (ground state)
- $\gamma$  dependence of formfactor  $F_{nn}$
- $\gamma$  dependence of level population  $P_n(\theta_0)$
- Beyond single potential well: periodic (100) Si channeling potential → band structure of transverse energy levels → more complicated calculations (e.g., in : BKP JETP Letters 2007)

## **Summary:** form-factors & populations change significantly.

![](_page_17_Picture_0.jpeg)

## **PXRC: Key parameters**

- Relativistic factor  $\gamma$  = number of quantum states (bands)
- Relativistic factor  $\gamma$  = form-factors of quantum states (bands)
- Relativistic factor  $\gamma$  = population of quantum states (bands)
- Angle of incidence  $\theta_0$  = population of quantum states
- Emission angle ( $\theta_{\nu}$  enters into form-factor)
- Reflection order → PXRC photon energy (enters formfactor)

# What is the best conditions for manifestation of "asymmetry" ? Answer: let study the $\delta$ - dependence on $\gamma$ and $\theta_0$

![](_page_18_Figure_1.jpeg)

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![](_page_19_Figure_1.jpeg)

Experimental and Theoretical Study of PXRC (Parametric X-Radiation at Channeling) from 255 MeV Electrons in Si 20

![](_page_20_Figure_1.jpeg)

Experimental and Theoretical Study of PXRC (Parametric X-Radiation at Channeling) from 255 MeV Electrons in Si 21

## Conclusions

- Recent experimental results (SAGA-LS Linac, JETP Letters 2012) on angular distributions of PXRC from channeling electrons with energy 255 MeV show deviations from ordinary PXR angular distribution
- Observed "asymmetry" is a quantum effect connected with "transverse" form-factors of channeled electrons
- Theory: strong correlation between number of quantum states in a potential well of crystallographic plane and maximums in asymmetry parameter delta
- Experiment was performed (unfortunately) at a gamma value when  $\delta$  = minimal
- Further experiments at SAGA-LS using thinner (dechanneling !) crystal and changing electron beam energy (exploring gammadependence) will bring new information

![](_page_22_Picture_0.jpeg)

# Thank you for attention !